FAIRCHILD
SEMICONDUCTOR®

IGBT

SGH15N120RUFD

Short Circuit Rated IGBT

General Description

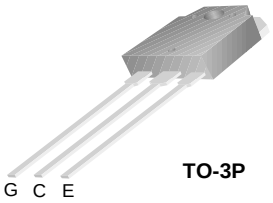
Fairchild's RUFD series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses as well as short circuit ruggedness. The RUFD series is designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

Features

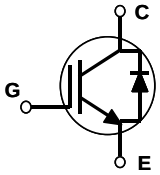
- Short circuit rated 10µs @ T_C = 100°C, V_{GE} = 15V
- High speed switching
- Low saturation voltage : $V_{CE(sat)}$ = 2.3 V @ I_C = 15A
- High input impedance
- CO-PAK, IGBT with FRD : t_{rr} = 70ns (typ.)

Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



TO-3P



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Description		SGH15N120RUFD	Units
V_{CES}	Collector-Emitter Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 25	V
I_C	Collector Current	@ T_C = 25°C	24	A
	Collector Current	@ T_C = 100°C	15	A
$I_{CM\ (1)}$	Pulsed Collector Current		45	A
I_F	Diode Continuous Forward Current	@ T_C = 100°C	15	A
I_{FM}	Diode Maximum Forward Current		90	A
T_{SC}	Short Circuit Withstand Time	@ T_C = 100°C	10	µs
P_D	Maximum Power Dissipation	@ T_C = 25°C	180	W
	Maximum Power Dissipation	@ T_C = 100°C	72	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes :
(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction-to-Case	--	0.69	°C/W
$R_{\theta JC}$(DIODE)	Thermal Resistance, Junction-to-Case	--	1.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 1mA	1200	--	--	V
$\Delta B_{VCES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	V_{GE} = 0V, I_C = 1mA	--	0.6	--	V/°C
I_{CES}	Collector Cut-Off Current	V_{CE} = V_{CES}, V_{GE} = 0V	--	--	1	mA
I_{GES}	G-E Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0V	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 15mA, V_{CE} = V_{GE}	3.5	5.5	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 15A, V_{GE} = 15V	--	2.3	3.0	V
		I_C = 24A, V_{GE} = 15V	--	2.8	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30V, V_{GE} = 0V, f = 1MHz	--	1400	--	pF
C_{oes}	Output Capacitance		--	135	--	pF
C_{res}	Reverse Transfer Capacitance		--	45	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 15A, R_G = 20Ω, V_{GE} = 15V, Inductive Load, T_C = 25°C	--	20	--	ns
t_r	Rise Time		--	60	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	110	ns
t_f	Fall Time		--	150	300	ns
E_{on}	Turn-On Switching Loss		--	1.0	--	mJ
E_{off}	Turn-Off Switching Loss		--	0.98	--	mJ
E_{ts}	Total Switching Loss		--	1.98	2.8	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 15A, R_G = 20Ω, V_{GE} = 15V, Inductive Load, T_C = 125°C	--	20	--	ns
t_r	Rise Time		--	70	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	80	150	ns
t_f	Fall Time		--	200	400	ns
E_{on}	Turn-On Switching Loss		--	1.13	--	mJ
E_{off}	Turn-Off Switching Loss		--	1.50	--	mJ
E_{ts}	Total Switching Loss		--	2.63	3.81	mJ
T_{sc}	Short Circuit Withstand Time	V_{CC} = 600 V, V_{GE} = 15V @ T_C = 100°C	10	--	--	µs
Q_g	Total Gate Charge	V_{CE} = 600 V, I_C = 15A, V_{GE} = 15V	--	72	108	nC
Q_{ge}	Gate-Emitter Charge		--	10	15	nC
Q_{gc}	Gate-Collector Charge		--	30	45	nC
Le	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

Electrical Characteristics of DIODE T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_{FM}	Diode Forward Voltage	I_F = 15A	T_C = 25°C	--	2.9	3.5	V
			T_C = 100°C	--	2.7	--	
t_{rr}	Diode Reverse Recovery Time	I_F = 15A dI/dt = 200 A/µs	T_C = 25°C	--	70	100	ns
			T_C = 100°C	--	85	--	
I_{rr}	Diode Peak Reverse Recovery Current		T_C = 25°C	--	7.0	9.0	A
			T_C = 100°C	--	8.5	--	
Q_{rr}	Diode Reverse Recovery Charge		T_C = 25°C	--	245	450	nC
			T_C = 100°C	--	360	--	

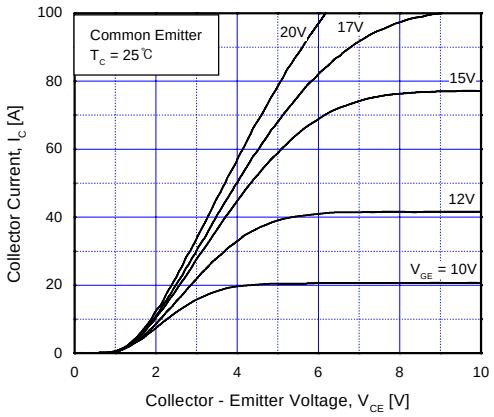


Fig 1. Typical Output Characteristics

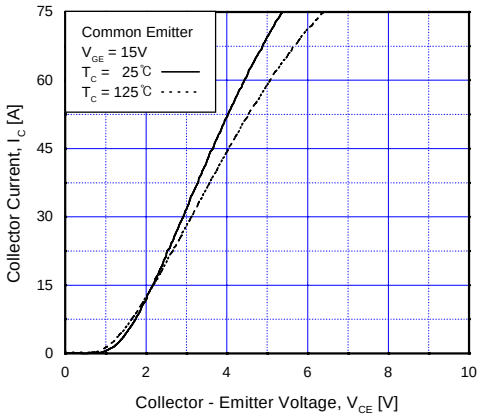


Fig 2. Typical Saturation Voltage Characteristics

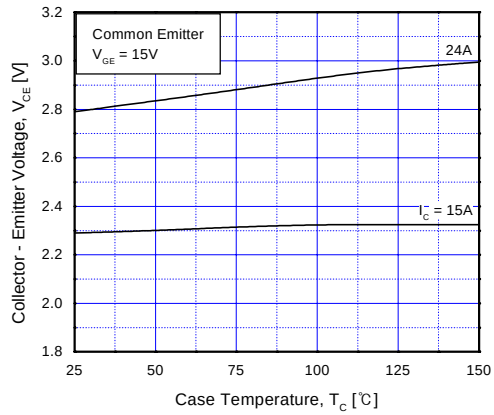


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

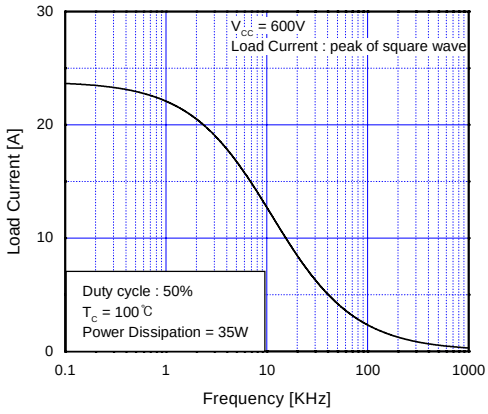


Fig 4. Load Current vs. Frequency

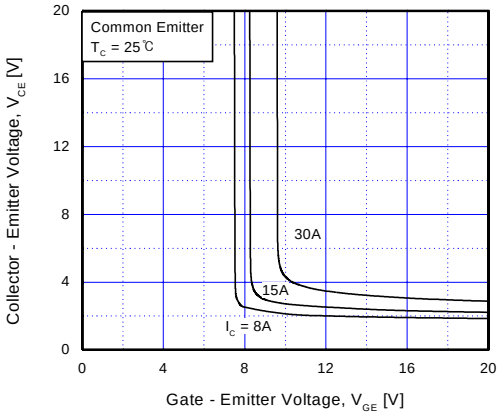


Fig 5. Saturation Voltage vs. V_{GE}

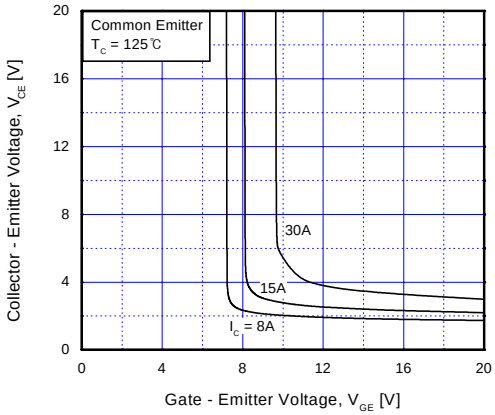


Fig 6. Saturation Voltage vs. V_{GE}

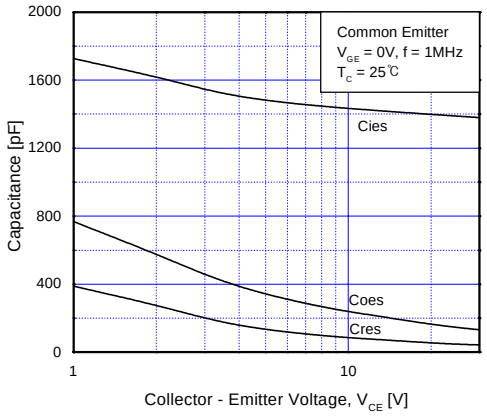


Fig 7. Capacitance Characteristics

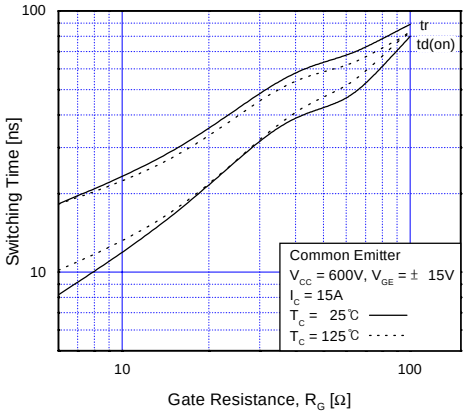


Fig 8. Turn-On Characteristics vs. Gate Resistance

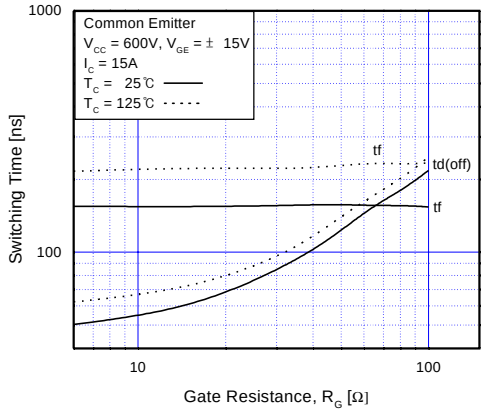


Fig 9. Turn-Off Characteristics vs. Gate Resistance

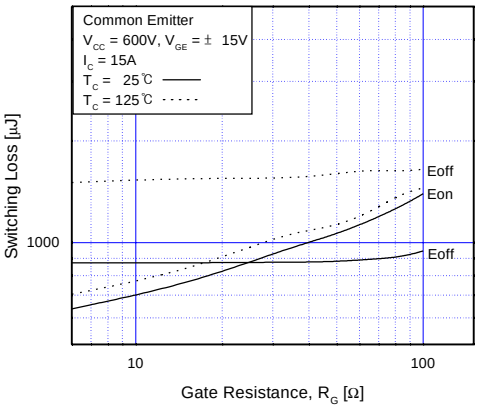


Fig 10. Switching Loss vs. Gate Resistance

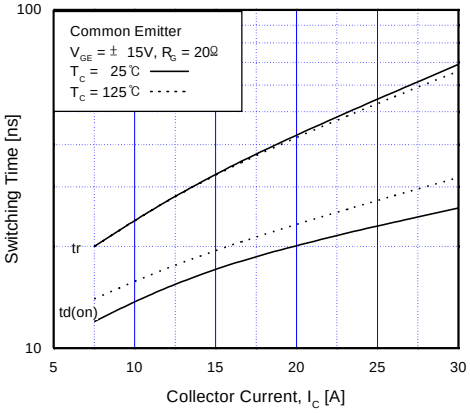


Fig 11. Turn-On Characteristics vs. Collector Current

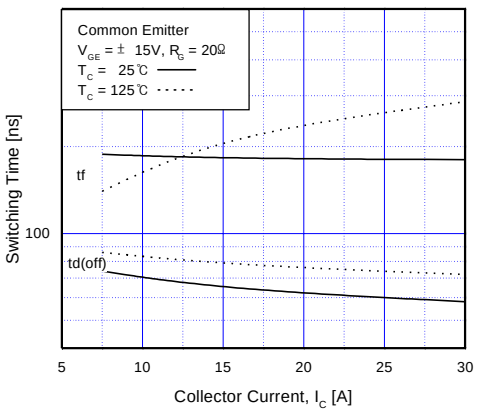


Fig 12. Turn-Off Characteristics vs. Collector Current

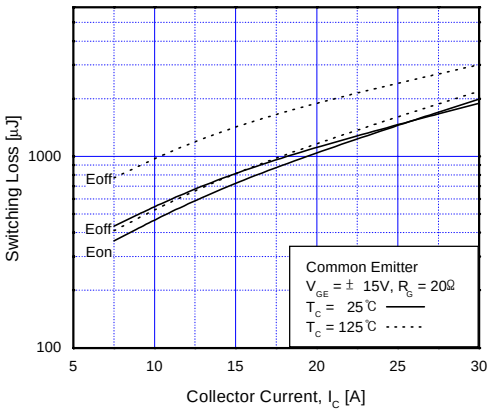


Fig 13. Switching Loss vs. Collector Current

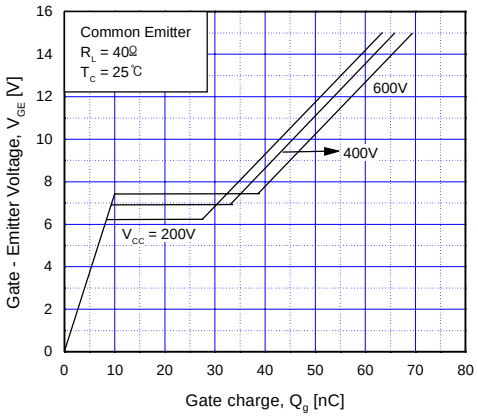


Fig 14. Gate Charge Characteristics

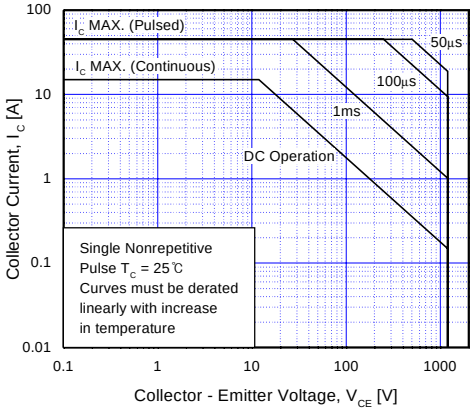


Fig 15. SOA Characteristics

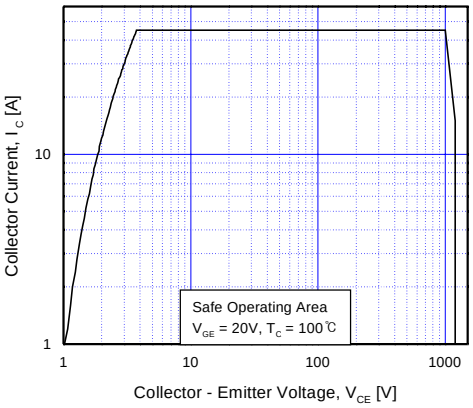


Fig 16. Turn-Off SOA

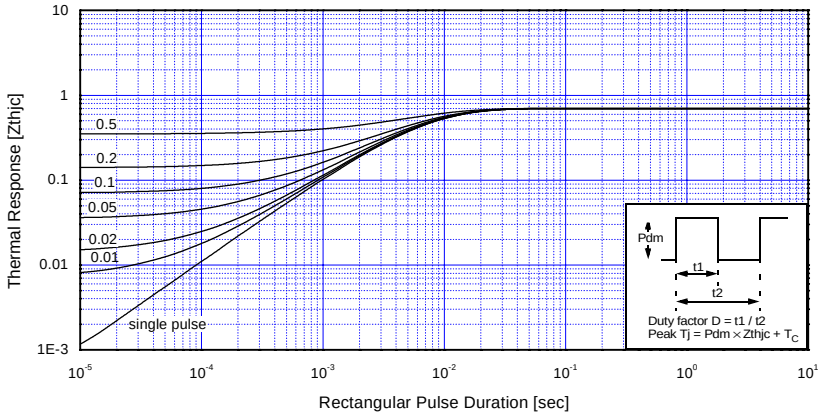


Fig 17. Transient Thermal Impedance of IGBT

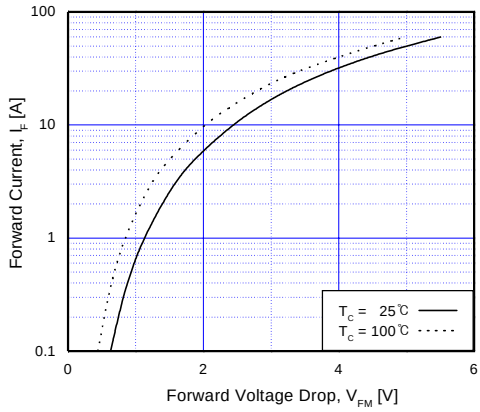


Fig 18. Forward Characteristics

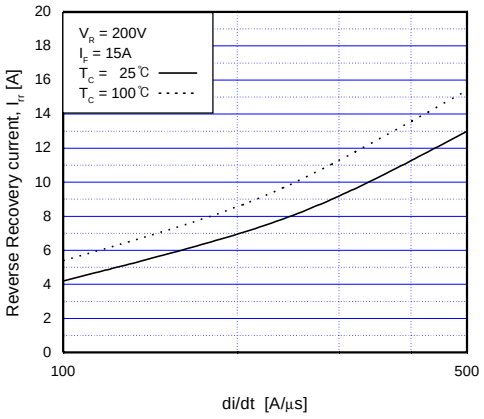


Fig 19. Reverse Recovery Current

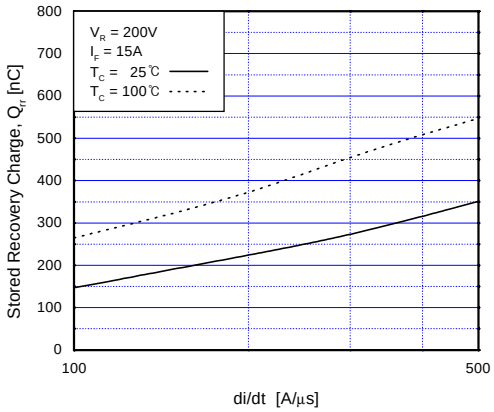


Fig 20. Stored Charge

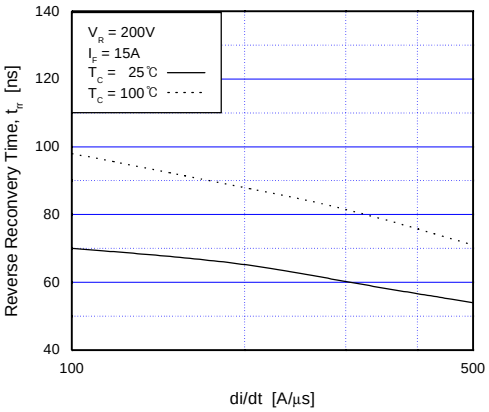
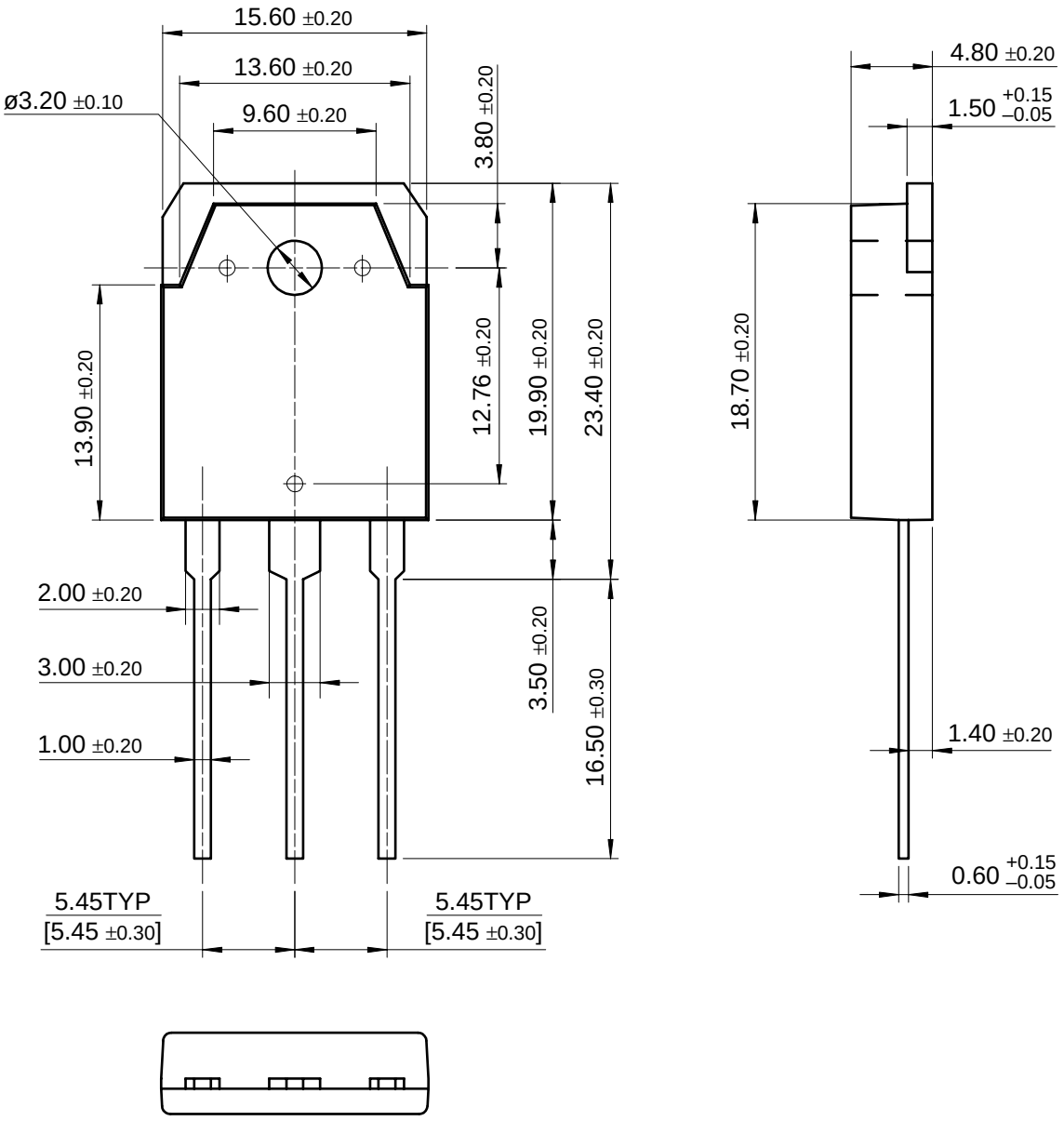


Fig 21. Reverse Recovery Time

Package Dimension

TO-3P (FS PKG CODE AF)



Dimensions in Millimeters

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Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

SGH15N120RUFD
Discrete, Short Circuit Rated IGBT with Diode

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General description

Fairchild's Insulated Gate Bipolar Transistor(IGBT) RUFD series provides low conduction and switching losses as well as short circuit ruggedness. RUFD series is designed for the applications such as motor control, UPS and general inverters where short-circuit ruggedness is required.

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Applications

AC &DC Motor controls, General Purpose Inverters, Robotics, Servo Controls

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Product status/pricing/packaging

Product	Product status	Pricing*	Inventory check & ordering	Package type	Leads	Packing method
SGH15N120RUFDTU	Full Production	$6.73	Purchase	TO-3P	3	RAIL

* Fairchild 1,000 piece Budgetary Pricing

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